



DMP3021SFVW

## 30V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

## Product Summarv

BV <sub>DSS</sub>	R <sub>DS(on)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
-30V	$15m\Omega @ V_{GS} = -10V$	-42A
-307	$25m\Omega @ V_{GS} = -5V$	-32A

## Description

This new generation MOSFET is designed to minimize the on-state resistance (RDS(on)) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

# Applications

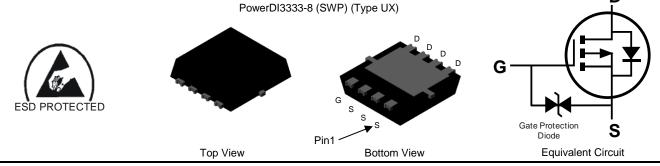
- General purpose interfacing switches
- Power management functions

## Features and Benefits

- Low R<sub>DS(on)</sub> ensures on-state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- **ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMP3021SFVWQ)

## **Mechanical Data**

- Package: PowerDI<sup>®</sup>3333-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish-Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (23)
- Weight: 0.072 grams (Approximate)



## Ordering Information (Note 4)

Part Number	Package	Packing		
Fart Nulliber	Гаскауе	Qty.	Carrier	
DMP3021SFVW-7	PowerDI3333-8 (SWP) (Type UX)	2,000	Tape & Reel	
DMP3021SFVW-13	PowerDI3333-8 (SWP) (Type UX)	3,000	Tape & Reel	

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. Notes:

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and

<1000ppm antimony compounds. 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



S2W = Product Type Marking Code YYWW = Date Code Marking  $\overline{YY}$  = Last Two Digits of Year (ex: 22 = 2022) WW = Week Code (01 to 53)

П



### Maximum Ratings (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage		VDSS	-30	V	
Gate-Source Voltage			V <sub>GSS</sub>	±25	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = -10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	-11 -9	A
Continuous Drain Current (Note 7) $V_{GS}$ = -10V	Steady State	Tc = +25°C Tc = +70°C	ID	-42 -34	А
Maximum Continuous Body Diode Forward Current (Note 7)			ls	-42	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			Ідм	-128	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I <sub>SM</sub>	-128	A
Avalanche Current (Note 8) L = 1mH			las	-13	A
Avalanche Energy (Note 8) L = 1mH			Eas	84	mJ

### Thermal Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	PD	1	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	126.6	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	PD	2.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>0JA</sub>	51.2	°C/W
Thermal Resistance, Junction to Case (Note 7)		Rejc	3.6	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

### Electrical Characteristics (@ TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)	•,		- 71-				
Drain-Source Breakdown Voltage	BVDSS	-30			V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_	_	-1	μA	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	lgss	_	_	±10	μA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.0	—	-2.5	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
Static Drain-Source On-Resistance	Dear	_	10.3	15		$V_{GS} = -10V, I_{D} = -8A$	
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	15.5	25	mΩ	$V_{GS} = -5V, I_{D} = -5A$	
Diode Forward Voltage	Vsd	_	-0.7	-1.2	V	$V_{GS} = 0V$ , $I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	_	1799	_	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	259	_	pF		
Reverse Transfer Capacitance	Crss	_	225	—	pF		
Gate Resistance	Rg	—	2.1	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = -5V)	Qg	_	17.4	—	nC		
Total Gate Charge (V <sub>GS</sub> = -10V)	Qg	_	34	_	nC		
Gate-Source Charge	Q <sub>gs</sub>	_	5.1	_	nC	V <sub>DS</sub> = -15V, I <sub>D</sub> = -10A	
Gate-Drain Charge	Q <sub>gd</sub>	_	8.4	_	nC	1	
Turn-On Delay Time	tD(on)	_	6.5	_	ns		
Turn-On Rise Time	tR	_	18.3	_	ns	V <sub>DD</sub> = -15V, V <sub>GS</sub> = -10V,	
Turn-Off Delay Time	tD(off)	_	35.8	—	ns	R <sub>G</sub> = 3Ω, I <sub>D</sub> = -10A	
Turn-Off Fall Time	tF		23.7		ns	7	
Reverse Recovery Time	trr		14.9		ns		
Reverse Recovery Charge	Qrr		15		nC	Is = -8A, dl/dt = 500A/µs	

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

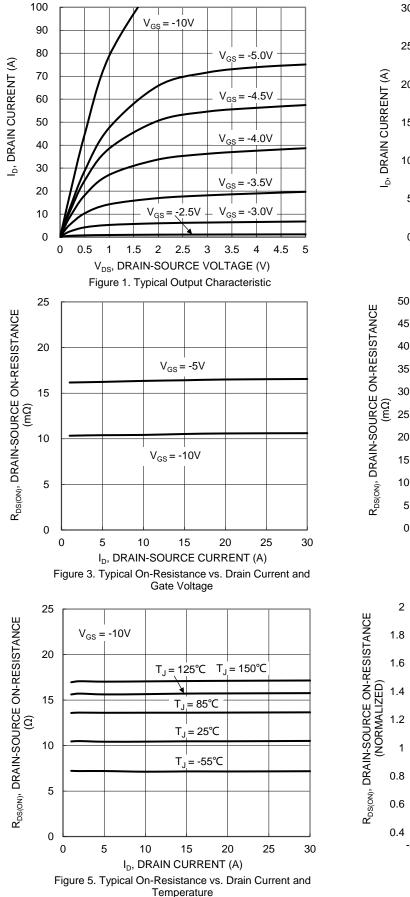
7. Thermal resistance from junction to soldering point (on the exposed drain pad).

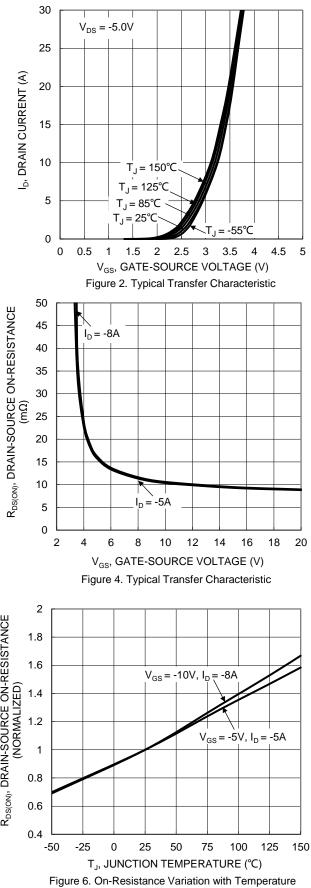
8. I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep  $T_J = +25^{\circ}C$ .

9. Short duration pulse test used to minimize self-heating effect.

10. Guaranteed by design. Not subject to product testing.

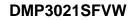


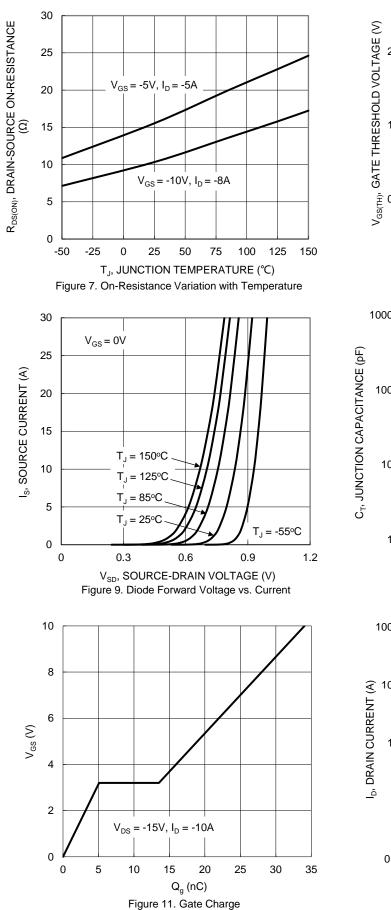


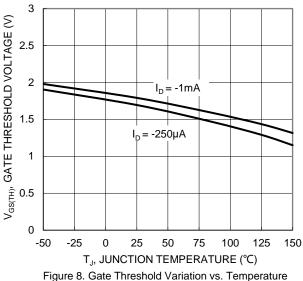


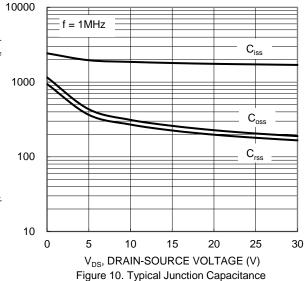
DMP3021SFVW Document number: DS43753 Rev. 2 - 2

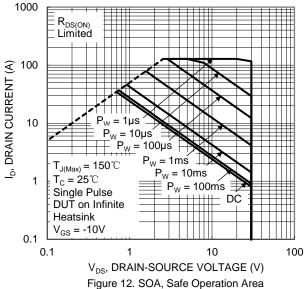




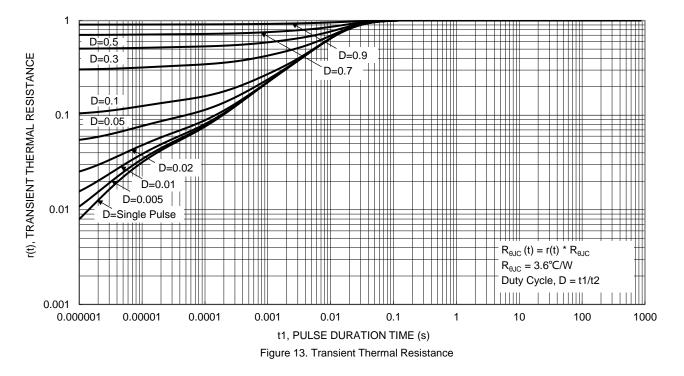








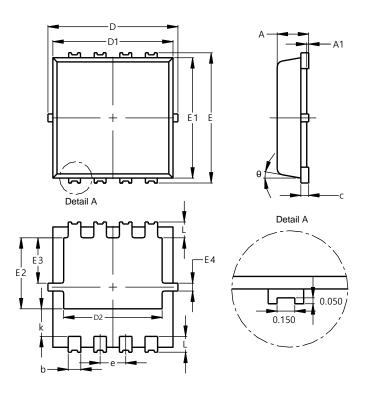






# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.



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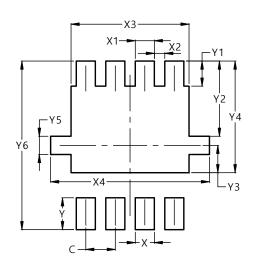
owerDI3333-8	(SWP)	(Type	(XII
Ower D13333-0	(SVVF)	(Type	UA)

Pow	PowerDI3333-8 (SWP)					
	(Type UX)					
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	-			
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
Е	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	_	_	0.65			
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All [	All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
X3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700



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